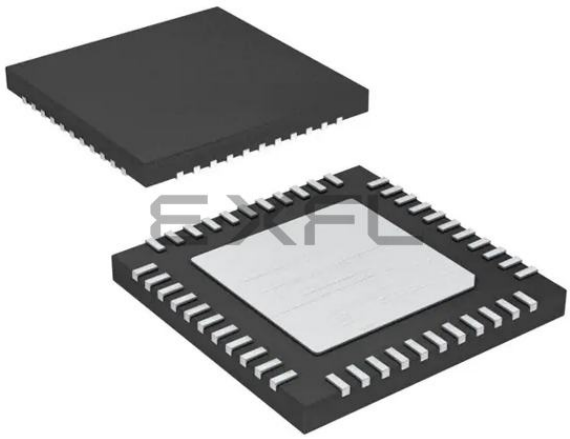

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	30 MIPs
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, Motor Control PWM, QEI, POR, PWM, WDT
Number of I/O	30
Program Memory Size	24KB (8K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VQFN Exposed Pad
Supplier Device Package	44-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3011t-30i-ml

3.0 PROGRAMMING EXECUTIVE APPLICATION

3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
  - Code memory and data EEPROM
  - Configuration registers
  - Device ID
- Erase memory
  - Bulk Erase by segment
  - Code memory (by row)
  - Data EEPROM (by row)
- Program memory
  - Code memory
  - Data EEPROM
  - Configuration registers
- Query
  - Blank Device
  - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in **Section 5.0 "Device Programming"**.

3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in Figure 4-1.

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in **Section 12.0 "Programming the Programming Executive to Memory"**.

Section 11.0 "ICSP™ Mode" describes the process for the ICSP programming method. **Section 11.13 "Reading the Application ID Word"** describes the procedure for reading the application ID word in ICSP mode.

FIGURE 4-1: CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE

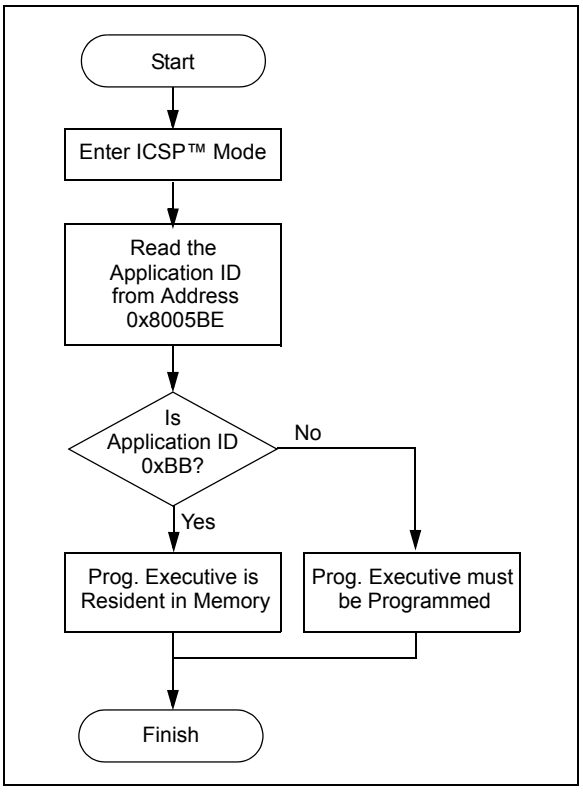

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TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)

Bit Field	Register	Description
FPR<4:0>	FOSC	**Alternate Oscillator Mode (when FOS<2:0> = 011b)** 1xxxx = Reserved (do not use) 0111x = Reserved (do not use) 01101 = Reserved (do not use) 01100 = ECIO – External clock. OSC2 pin is I/O 01011 = EC – External clock. OSC2 pin is system clock output (FOSC/4) 01010 = Reserved (do not use) 01001 = ERC – External RC oscillator. OSC2 pin is system clock output (FOSC/4) 01000 = ERCIO – External RC oscillator. OSC2 pin is I/O 00111 = Reserved (do not use) 00110 = Reserved (do not use) 00101 = Reserved (do not use) 00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal) 00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal) 00001 = Reserved (do not use) 00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal)

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8.5 Command Descriptions

All commands that are supported by the programming executive are described in **Section 8.5.1 "SCHECK Command"** through **Section 8.5.11 "QVER Command"**.

8.5.1 SCHECK COMMAND

15 12	11 0
Opcode	Length

Field	Description
Opcode	0x0
Length	0x1

The SCHECK command instructs the programming executive to do nothing, but generate a response. This command is used as a "sanity check" to verify that the programming executive is operational.

Expected Response (2 words):
0x1000
0x0002

Note:	This instruction is not required for programming, but is provided for development purposes only.

8.5.2 READD COMMAND

15 12	11 8	7 0
Opcode	Length	
Reserved0	N	
Reserved1		Addr_MSB
Addr_LS		

Field	Description
Opcode	0x1
Length	0x4
Reserved0	0x0
N	Number of 16-bit words to read (max of 2048)
Reserved1	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The READD command instructs the programming executive to read N 16-bit words of memory starting from the 24-bit address specified by Addr_MSB and Addr_LS. This command can only be used to read 16-bit data. It can be used to read data EEPROM, Configuration registers and the device ID.

Expected Response (2+N words):
0x1100
N + 2
Data word 1
...
Data word N

Note:	Reading unimplemented memory will cause the programming executive to reset.

8.5.11 QVER COMMAND

15 12	11 0
Opcode	Length

Field	Description
Opcode	0xB
Length	0x1

The QVER command queries the version of the programming executive software stored in test memory. The “version.revision” information is returned in the response’s QE_Code using a single byte with the following format: main version in upper nibble and revision in the lower nibble (i.e., 0x23 is version 2.3 of programming executive software).

Expected Response (2 words):
0x1BMN (where “MN” stands for version M.N)
0x0002

9.0 PROGRAMMING EXECUTIVE RESPONSES

9.1 Overview

The programming executive sends a response to the programmer for each command that it receives. The response indicates if the command was processed correctly, and includes any required response or error data.

The programming executive response set is shown in Table 9-1. This table contains the opcode, mnemonic and description for each response. The response format is described in **Section 9.2 “Response Format”**.

TABLE 9-1: PROGRAMMING EXECUTIVE RESPONSE SET

Opcode	Mnemonic	Description
0x1	PASS	Command successfully processed.
0x2	FAIL	Command unsuccessfully processed.
0x3	NACK	Command not known.

9.2 Response Format

As shown in Example 9-1, all programming executive responses have a general format consisting of a two word header and any required data for the command. Table 9-2 lists the fields and their descriptions.

EXAMPLE 9-1: FORMAT

15 12	11 8	7 0
Opcode	Last_Cmd	QE_Code
Length		
D_1 (if applicable)		
...		
D_N (if applicable)		

TABLE 9-2: FIELDS AND DESCRIPTIONS

Field	Description
Opcode	Response opcode.
Last_Cmd	Programmer command that generated the response.
QE_Code	Query code or Error code.
Length	Response length in 16-bit words (includes 2 header words.)
D_1	First 16-bit data word (if applicable).
D_N	Last 16-bit data word (if applicable).

9.2.1 Opcode FIELD

The Opcode is a 4-bit field in the first word of the response. The Opcode indicates how the command was processed (see Table 9-1). If the command is processed successfully, the response opcode is PASS. If there is an error in processing the command, the response opcode is FAIL, and the QE_Code indicates the reason for the failure. If the command sent to the programming executive is not identified, the programming executive returns a NACK response.

9.2.2 Last_Cmd FIELD

The Last_Cmd is a 4-bit field in the first word of the response and indicates the command that the programming executive processed. Since the programming executive can only process one command at a time, this field is technically not required. However, it can be used to verify whether the programming executive correctly received the command that the programmer transmitted.

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11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIHH (high voltage), and then performing additional steps as illustrated in Figure 11-4.

Note 1: The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.

2: Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).

3: Before leaving the Reset vector, execute two GOTO instructions, followed by a single NOP instruction must be executed.

FIGURE 11-4: ENTERING ICSP™ MODE

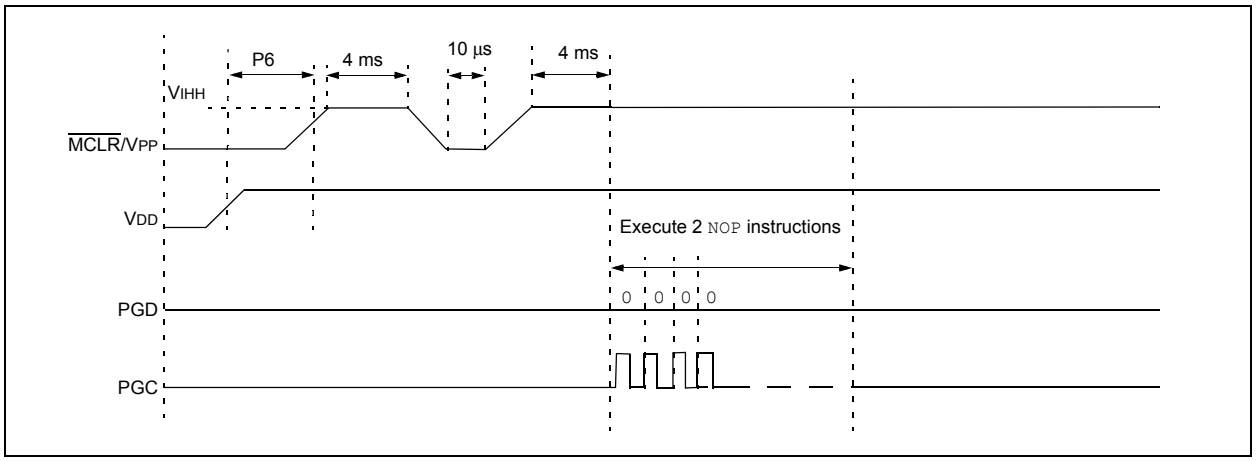

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TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 11: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

11.6 Erasing Program Memory in Low-Voltage Systems

The procedure for erasing program memory (all code memory and data memory) in low-voltage systems (with VDD between 2.5 volts and 4.5 volts) is quite different than the procedure for erasing program memory in normal-voltage systems. Instead of using a Bulk Erase operation, each region of memory must be individually erased by row. Namely, all of the code memory, executive memory and data memory must be erased one row at a time. This procedure is detailed in Table 11-5.

Due to security restrictions, the FBS, FSS and FGS register cannot be erased in low-voltage systems. Once any bits in the FGS register are programmed to '0', they can only be set back to '1' by performing a Bulk Erase in a normal-voltage system. Alternatively, a Segment Erase operation can be performed instead of a Bulk Erase.

Normal-voltage systems can also be used to erase program memory as shown in Table 11-5. However, since this method is more time-consuming and does not clear the code-protect bits, it is not recommended.

Note: Program memory must be erased before writing any data to program memory.

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize NVMADR and NVMADRU to erase code memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	883B26	MOV W6, NVMADRU
0000	200407	MOV #0x40, W7
Step 3: Set NVMCON to erase 1 row of code memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 4: Unlock the NVMCON to erase 1 row of code memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 5: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
–	–	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP

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TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 6: Update the row address stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be incremented.		
0000	430307	ADD W6, W7, W6
0000	AF0042	BTSC SR, #C
0000	EC2764	INC NVMADRU
0000	883B16	MOV W6, NVMADR
Step 7: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 8: Repeat Steps 3-7 until all rows of code memory are erased.		
Step 9: Initialize NVMADR and NVMADRU to erase executive memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	200807	MOV #0x80, W7
0000	883B27	MOV W7, NVMADRU
0000	200407	MOV #0x40, W7
Step 10: Set NVMCON to erase 1 row of executive memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 11: Unlock the NVMCON to erase 1 row of executive memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 12: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 13: Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
Step 14: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 15: Repeat Steps 10-14 until all 24 rows of executive memory are erased.		
Step 16: Initialize NVMADR and NVMADRU to erase data memory and initialize W7 for row address updates.		
0000	2XXXX6	MOV #<lower 16-bits of starting Data EEPROM address>, W6
0000	883B16	MOV W6, NVMADR
0000	2007F6	MOV #0x7F, W6
0000	883B16	MOV W6, NVMADRU
0000	200207	MOV #0x20, W7
Step 17: Set NVMCON to erase 1 row of data memory.		
0000	24075A	MOV #0x4075, W10
0000	883B0A	MOV W10, NVMCON

11.7 Writing Configuration Memory

The FOSC, FWDT, FBORPOR and FICD registers are not erasable. It is recommended that all Configuration registers be set to a default value after erasing program memory. The FWDT, FBORPOR and FICD registers can be set to a default all '1's value by programming 0xFFFF to each register. Since these registers contain unimplemented bits that read as '0' the default values shown in Table 11-6 will be read instead of 0xFFFF. The recommended default FOSC value is 0xC100, which selects the FRC clock oscillator setting.

The FGS, FBS and FSS Configuration registers are special since they enable code protection for the device. For security purposes, once any bit in these registers is programmed to '0' (to enable some code protection feature), it can only be set back to '1' by performing a Bulk Erase or Segment Erase as described in **Section 11.5 "Erasing Program Memory in Normal-Voltage Systems"**. Programming these bits from a '0' to '1' is not possible, but they may be programmed from a '1' to a '0' to enable code protection.

Table 11-7 shows the ICSP programming details for clearing the Configuration registers. In Step 1, the Reset vector is exited. In Step 2, the write pointer (W7) is loaded with 0x0000, which is the original destination address (in TBLPAG 0xF8 of program memory). In Step 3, the NVMCON is set to program one Configuration register. In Step 4, the TBLPAG register is initialized, to 0xF8, for writing to the Configuration registers. In Step 5, the value to write to the each Configuration register (0xFFFF) is loaded to W6. In Step 6, the Configuration register data is written to the write latch using the TBLWTL instruction. In Steps 7 and 8, the NVMCON is unlocked for programming and the programming cycle is initiated, as described in **Section 11.4 "Flash Memory Programming in ICSP Mode"**. In Step 9, the internal PC is set to 0x100 as a safety measure to prevent the PC from incrementing into unimplemented memory. Lastly, Steps 3-9 are repeated six times until all seven Configuration registers are cleared.

TABLE 11-6: DEFAULT CONFIGURATION REGISTER VALUES

Address	Register	Default Value
0xF80000	FOSC	0xC100
0xF80002	FWDT	0x803F
0xF80004	FBORPOR	0x87B3
0xF80006	FBS	0x310F
0xF80008	FSS	0x330F
0xF8000A	FGS	0x0007
0xF8000C	FICD	0xC003

TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Initialize the write pointer (W7) for the TBLWT instruction.		
0000	200007	MOV #0x0000, W7
Step 3: Set the NVMCON to program 1 Configuration register.		
0000 0000	24008A 883B0A	MOV #0x4008, W10 MOV W10, NVMCON
Step 4: Initialize the TBLPAG register.		
0000 0000	200F80 880190	MOV #0xF8, W0 MOV W0, TBLPAG
Step 5: Load the Configuration register data to W6.		
0000 0000	2xxxx0 000000	MOV #<CONFIG_VALUE>, W0 NOP

11.8 Writing Code Memory

The procedure for writing code memory is similar to the procedure for clearing the Configuration registers, except that 32 instruction words are programmed at a time. To facilitate this operation, working registers W0:W5 are used as temporary holding registers for the data to be programmed.

Table 11-8 shows the ICSP programming details, including the serial pattern with the ICSP command code, which must be transmitted Least Significant bit first using the PGC and PGD pins (see Figure 11-2). In Step 1, the Reset vector is exited. In Step 2, the NVMCON register is initialized for single-panel programming of code memory. In Step 3, the 24-bit starting destination address for programming is loaded into the TBLPAG register and W7 register. The upper byte of the starting destination address is stored to TBLPAG, while the lower 16 bits of the destination address are stored to W7.

To minimize the programming time, the same packed instruction format that the programming executive uses is utilized (Figure 8-2). In Step 4, four packed instruction words are stored to working registers W0:W5 using the `MOV` instruction and the read pointer W6 is initialized. The contents of W0:W5 holding the packed instruction word data is shown in Figure 11-4.

In Step 5, eight `TBLWT` instructions are used to copy the data from W0:W5 to the write latches of code memory. Since code memory is programmed 32 instruction words at a time, Steps 4 and 5 are repeated eight times to load all the write latches (Step 6).

After the write latches are loaded, programming is initiated by writing to the NVMKEY and NVMCON registers in Steps 7 and 8. In Step 9, the internal PC is reset to 0x100. This is a precautionary measure to prevent the PC from incrementing into unimplemented memory when large devices are being programmed. Lastly, in Step 10, Steps 2-9 are repeated until all of code memory is programmed.

FIGURE 11-5: PACKED INSTRUCTION WORDS IN W0:W5

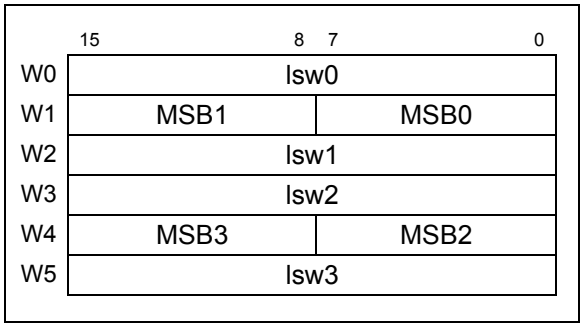

TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Set the NVMCON to program 32 instruction words.		
0000 0000	24001A 883B0A	MOV #0x4001, W10 MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for `TBLWT` instruction.		

0000
0000
0000
	200xx0
	880190
	2xxxx7
		MOV #<DestinationAddress23:16>, W0
		MOV W0, TBLPAG
		MOV #<DestinationAddress15:0>, W7

Step 4: Initialize the read pointer (W6) and load W0:W5 with the next 4 instruction words to program.		

0000
0000
0000
0000
0000
0000
	2xxxx0
	2xxxx1
	2xxxx2
	2xxxx3
	2xxxx4
	2xxxx5
		MOV #<LSW0>, W0
		MOV #<MSB1:MSB0>, W1
		MOV #<LSW1>, W2
		MOV #<LSW2>, W3
		MOV #<MSB3:MSB2>, W4
		MOV #<LSW3>, W5

11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Set the NVMCON to write 16 data words.		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for TBLWT instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
Step 4: Load W0:W3 with the next 4 data words to program.		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.		

11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat steps 3-5 until all desired data memory is read.		

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11.13 Reading the Application ID Word

The application ID word is stored at address 0x8005BE in executive code memory. To read this memory location, you must use the SIX control code to move this program memory location to the VISI register. The REGOUT control code must then be used to clock the contents of the VISI register out of the device. The corresponding control and instruction codes that must be serially transmitted to the device to perform this operation are shown in Table 11-13.

Once the programmer has clocked-out the application ID word, it must be inspected. If the application ID has the value 0xBB, the programming executive is resident in memory and the device can be programmed using the mechanism described in **Section 5.0 "Device Programming"**. However, if the application ID has any other value, the programming executive is not resident in memory. It must be loaded to memory before the device can be programmed. The procedure for loading the programming executive to the memory is described in **Section 12.0 "Programming the Programming Executive to Memory"**.

11.14 Exiting ICSP Mode

After confirming that the programming executive is resident in memory, or loading the programming executive, ICSP mode is exited by removing power to the device or bringing $\overline{MCLR}$ to V_{IL}. Programming can then take place by following the procedure outlined in **Section 5.0 "Device Programming"**.

TABLE 11-13: SERIAL INSTRUCTION EXECUTION FOR READING THE APPLICATION ID WORD

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W0) for TBLRD instruction.		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	205BE0	MOV #0x5BE, W0
0000	207841	MOV VISI, W1
0000	000000	NOP
0000	BA0890	TBLRDL [W0], [W1]
0000	000000	NOP
0000	000000	NOP
Step 3: Output the VISI register using the REGOUT command.		
0001	<VISI>	Clock out contents of the VISI register
0000	000000	NOP

12.0 PROGRAMMING THE PROGRAMMING EXECUTIVE TO MEMORY

12.1 Overview

If it is determined that the programming executive does not reside in executive memory (as described in **Section 4.0 "Confirming the Contents of Executive Memory"**), it must be programmed into executive memory using ICSP and the techniques described in **Section 11.0 "ICSP™ Mode"**.

Storing the programming executive to executive memory is similar to normal programming of code memory. The executive memory must first be erased, and then the programming executive must be programmed 32 words at a time. This control flow is summarized in Table 12-1.

TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector and erase executive memory.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize the NVMCON to erase executive memory.		
0000	24072A	MOV #0x4072, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 4: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #15
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #15
0000	000000	NOP
0000	000000	NOP
Step 5: Initialize the TBLPAG and the write pointer (W7).		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	EB0380	CLR W7
0000	000000	NOP
0000	000000	NOP
Step 6: Initialize the NVMCON to program 32 instruction words.		
0000	24001A	MOV #0x4001, W10
0000	883B0A	MOV W10, NVMCON
Step 7: Load W0:W5 with the next 4 words of packed programming executive code and initialize W6 for programming. Programming starts from the base of executive memory (0x800000) using W6 as a read pointer and W7 as a write pointer.		
0000	2<LSW0>0	MOV #<LSW0>, W0
0000	2<MSB1:MSB0>1	MOV #<MSB1:MSB0>, W1
0000	2<LSW1>2	MOV #<LSW1>, W2
0000	2<LSW2>3	MOV #<LSW2>, W3
0000	2<MSB3:MSB2>4	MOV #<MSB3:MSB2>, W4
0000	2<LSW3>5	MOV #<LSW3>, W5

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TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 8: Set the read pointer (W6) and load the (next four write) latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 9: Repeat Steps 7-8 eight times to load the write latches for the 32 instructions.		
Step 10: Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 11: Initiate the programming cycle.		
0000	A8E761	BSET NVMCON, #15
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #15
0000	000000	NOP
0000	000000	NOP
Step 12: Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 13: Repeat Steps 7-12 until all 23 rows of executive memory are programmed.		

TABLE 12-2: READING EXECUTIVE MEMORY (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
Step 5: Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat Steps 3-5 until all 736 instruction words of executive memory are read.		

TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	**Sym**	**Characteristic**	**Min**	**Max**	**Units**	**Conditions**
P9b	TDLY5	Delay between PGD ↓by programming executive to PGD released by programming executive	15	—	µs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	µs	—
P11	TDLY7	Delay between clocking out response words	10	—	µs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode

APPENDIX A: DEVICE-SPECIFIC INFORMATION

A.1 Checksum Computation

The checksum computation is described in **Section 6.8 "Checksum Computation"**. Table A-1 shows how this 16-bit computation can be made for each dsPIC30F device. Computations for read code protection are shown both enabled and disabled. The checksum values assume that the Configuration registers are also erased. However, when code protection is enabled, the value of the FGS register is assumed to be 0x5.

A.2 dsPIC30F5011 and dsPIC30F5013

A.2.1 ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 before the device is chip erased. The steps to perform this action are shown in Table 11-4.

A.2.2 ENHANCED ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 using the `PROGC` command before the `ERASEB` command is used to erase the chip.

TABLE A-1: CHECKSUM COMPUTATION

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F2010	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2011	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2012	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3010	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3011	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3012	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3013	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3014	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4011	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4012	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4013	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5011	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5013	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5015	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404

Item Description:

SUM(a:b) = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

CFGB = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

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ISBN: 978-1-60932-636-4

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